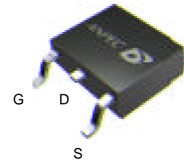
N-Channel Enhancement Mode MOSFET

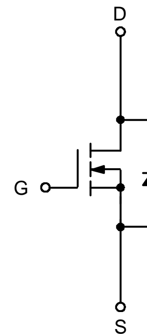
Features

- 30V/30A,
  $R_{DS(ON)}$=15mΩ (typ.) @ V_{GS}=10V
  $R_{DS(ON)}$=22mΩ (typ.) @ V_{GS}=4.5V
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free Available (RoHS Compliant)

Pin Description



Top View of TO-252

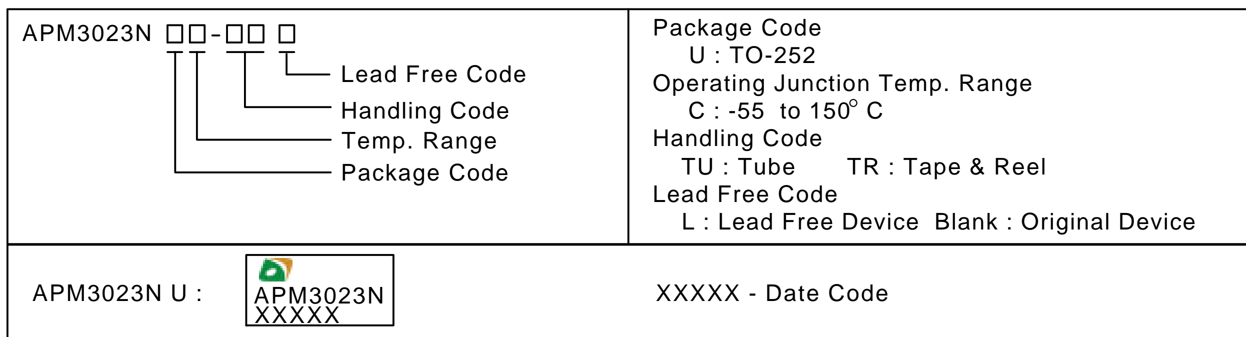


N-Channel MOSFET

Applications

- Power Management in Desktop Computer or DC/DC Converters

Ordering and Marking Information



APM3023N □□-□□ □ (Lead Free Code; Handling Code; Temp. Range; Package Code)	Package Code U : TO-252 Operating Junction Temp. Range C : -55 to 150° C Handling Code TU : Tube TR : Tape & Reel Lead Free Code L : Lead Free Device Blank : Original Device
APM3023N U : APM3023N XXXXX	XXXXX - Date Code

Note: ANPEC lead-free products contain molding compounds and 100% matte tin plate termination finish; which are fully compliant with RoHS and compatible with both SnPb and lead-free soldiering operations. ANPEC lead-free products meet or exceed the lead-free requirements of IPC/JEDEC J STD-020C for MSL classification at lead-free peak reflow temperature.

ANPEC reserves the right to make changes to improve reliability or manufacturability without notice, and advise customers to obtain the latest version of relevant information to verify before placing orders.

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (T_A=25°C Unless Otherwise Noted)				
V_{DSS}	Drain-Source Voltage		30	V
V_{GSS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		-55 to 150	°C
I_S	Diode Continuous Forward Current	T_C=25°C	20	A
Mounted on Large Heat Sink				
I_{DP}	300μs Pulse Drain Current Tested	T_C=25°C	100	A
		T_C=100°C	60	
I_D	Continuous Drain Current	T_C=25°C	30*	A
		T_C=100°C	20	
P_D	Maximum Power Dissipation	T_C=25°C	50	W
		T_C=100°C	20	
$R_{\theta JC}$	Thermal Resistance-Junction to Case		2.5	°C/W
Mounted on PCB of 1in^2 Pad Area				
I_{DP}	300μs Pulse Drain Current Tested	T_A=25°C	100	A
		T_A=100°C	60	
I_D	Continuous Drain Current	T_A=25°C	10	A
		T_A=100°C	4	
P_D	Maximum Power Dissipation	T_A=25°C	2.5	W
		T_A=100°C	1	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		50	°C/W
Mounted on PCB of Minimum Footprint				
I_{DP}	300μs Pulse Drain Current Tested	T_A=25°C	100	A
		T_A=100°C	60	
I_D	Continuous Drain Current	T_A=25°C	7	A
		T_A=100°C	5	
P_D	Maximum Power Dissipation	T_A=25°C	1.6	W
		T_A=100°C	0.6	
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient		75	°C/W

Note:

* Current limited by bond wire.

Copyright © ANPEC Electronics Corp.

Electrical Characteristics (T_A = 25°C unless otherwise noted)

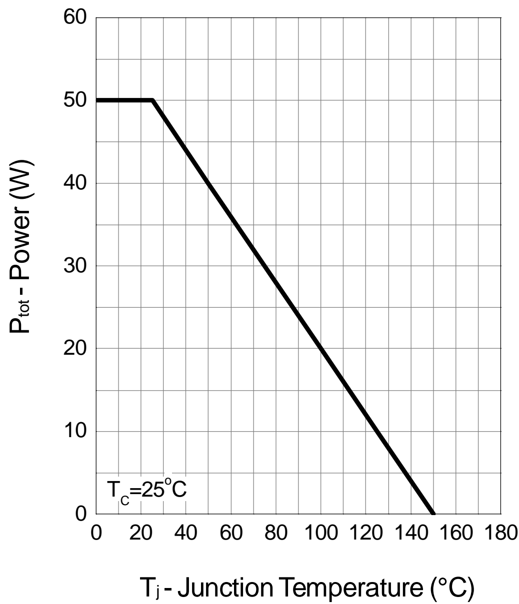
Symbol	Parameter	Test Condition	APM3023NU			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_{DS}=250μA	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=24V, V_{GS}=0V			1	μA
		T_J=85°C			30	
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_{DS}=250μA	1	1.5	2	V
I_{GSS}	Gate Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$R_{DS(ON)}$ [a]	Drain-Source On-state Resistance	V_{GS}=10V, I_{DS}=20A		15	20	mΩ
		V_{GS}=4.5V, I_{DS}=10A		22	28	
Diode Characteristics						
V_{SD} [a]	Diode Forward Voltage	I_{SD}=15A, V_{GS}=0V		0.7	1.3	V
Dynamic Characteristics [b]						
R_G	Gate Resistance	V_{GS}=0V,V_{DS}=0V,F=1MHz		2.5		Ω
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=25V, Frequency=1.0MHz		1040		pF
C_{oss}	Output Capacitance			200		
C_{rss}	Reverse Transfer Capacitance			85		
$t_{d(ON)}$	Turn-on Delay Time	V_{DD}=15V, R_L=15Ω, I_{DS}=1A, V_{GEN}=10V, R_G=6Ω		11	18	ns
T_r	Turn-on Rise Time			17	26	
$t_{d(OFF)}$	Turn-off Delay Time			37	54	
T_f	Turn-off Fall Time			20	30	
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=100A/μs		12.1		
T_{rr}	Body Diode Reverse Recovery Time			22		
Gate Charge Characteristics [b]						
Q_g	Total Gate Charge	V_{DS}=15V, V_{GS}=10V, I_{DS}=20A		30	40	nC
Q_{gs}	Gate-Source Charge			5.8		
Q_{gd}	Gate-Drain Charge			3.8		

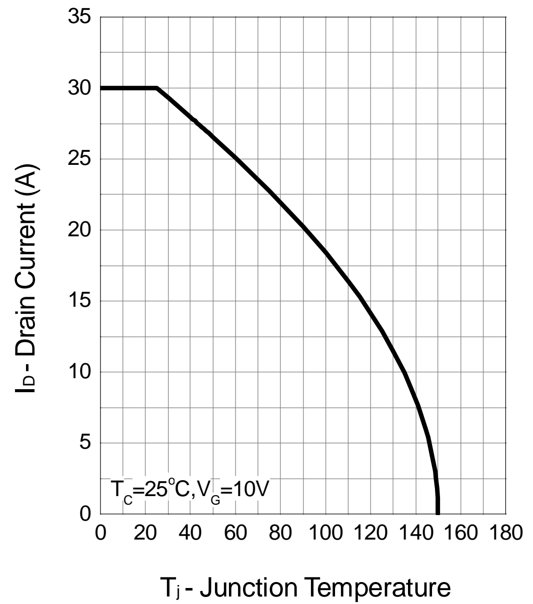
Notes:

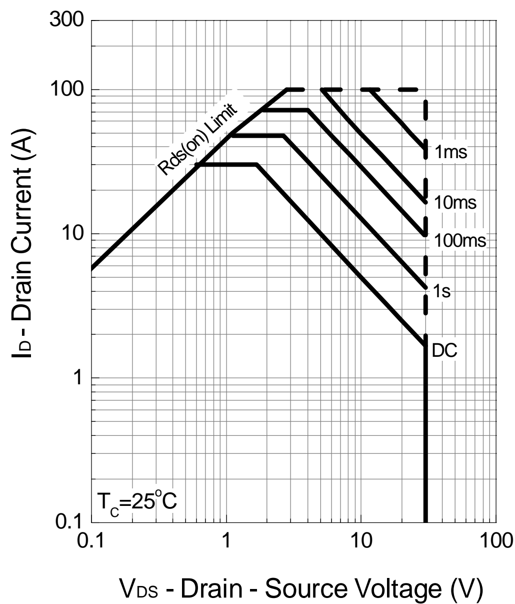
a : Pulse test ; pulse width≤300μs, duty cycle≤2%.
b : Guaranteed by design, not subject to production testing.

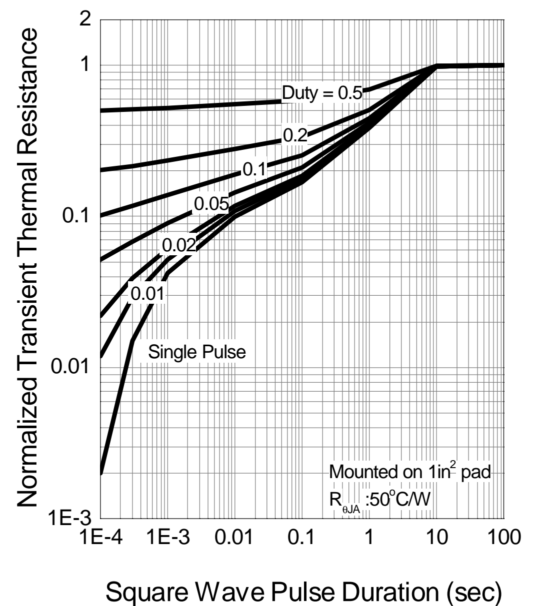
Copyright © ANPEC Electronics Corp.

Typical Characteristics

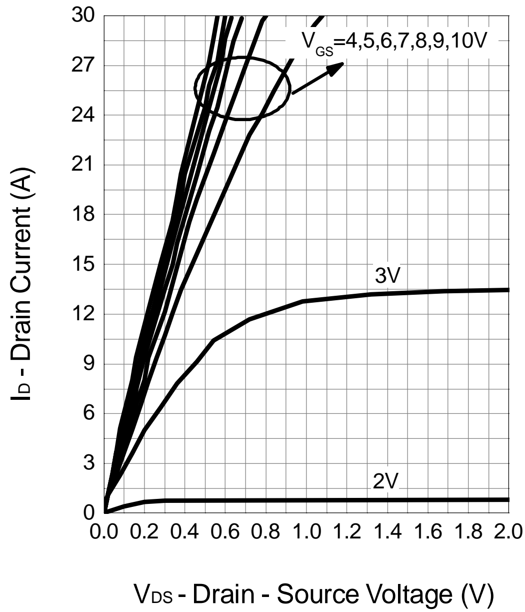


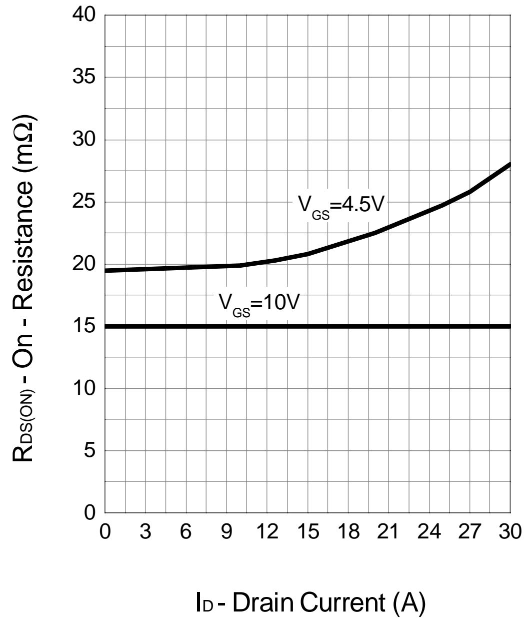


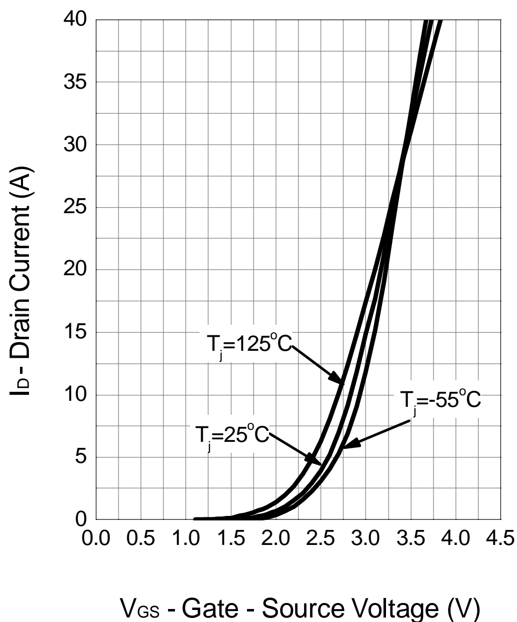


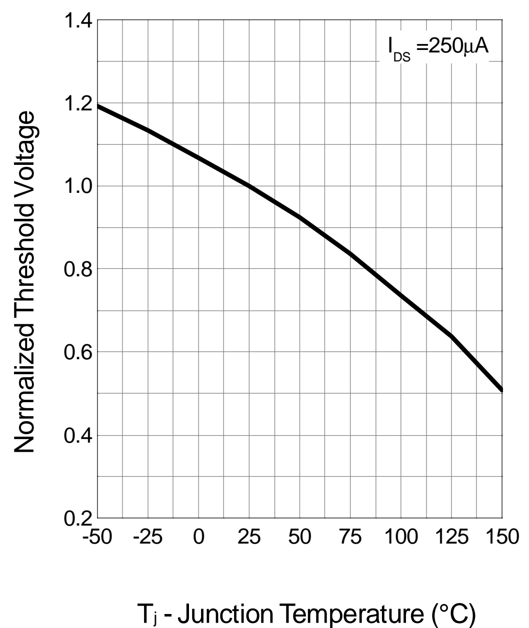


Typical Characteristics (Cont.)

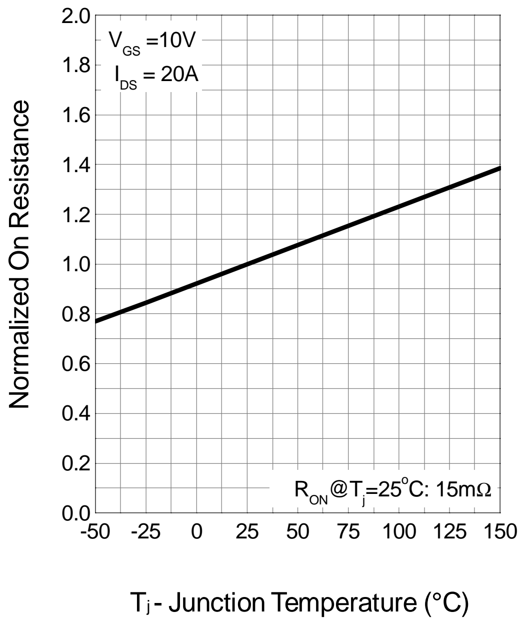


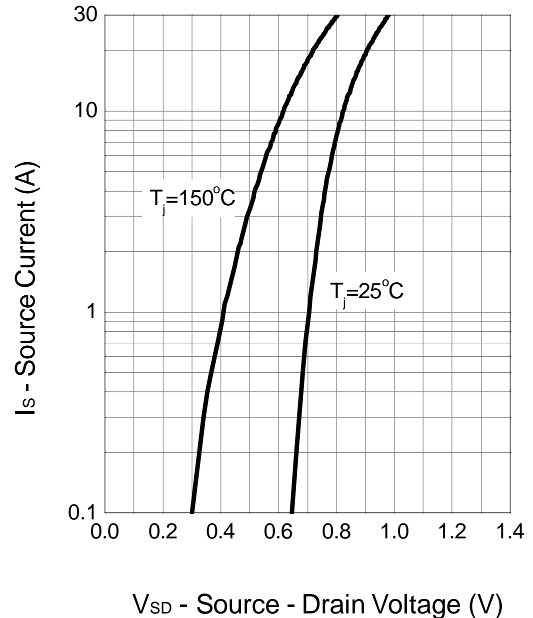


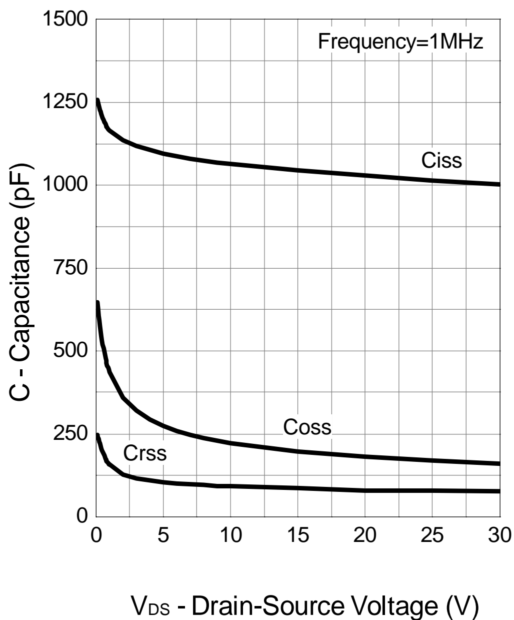


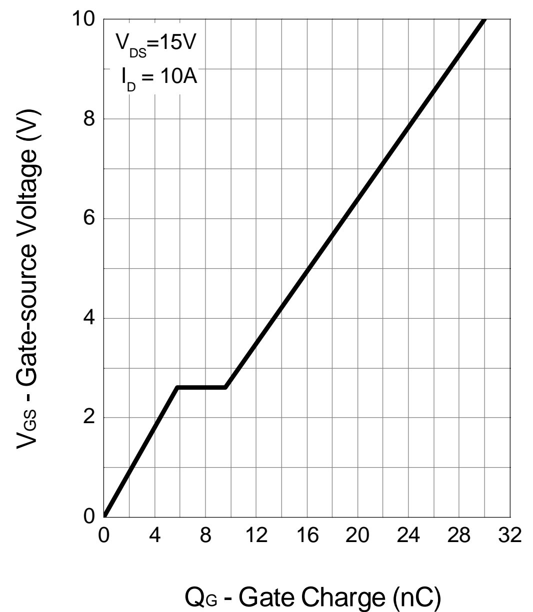


Typical Characteristics (Cont.)





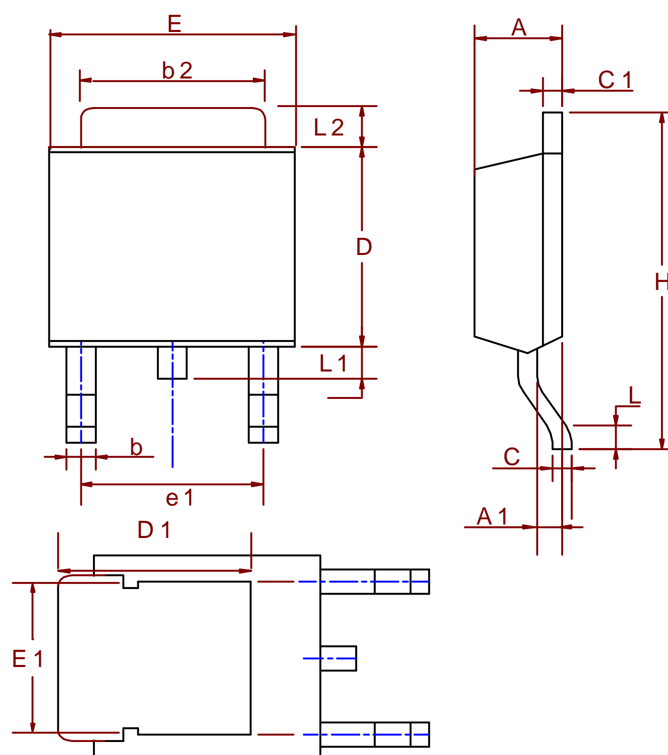




Copyright © ANPEC Electronics Corp.

Package Information

TO-252 (Reference JEDEC Registration TO-252)



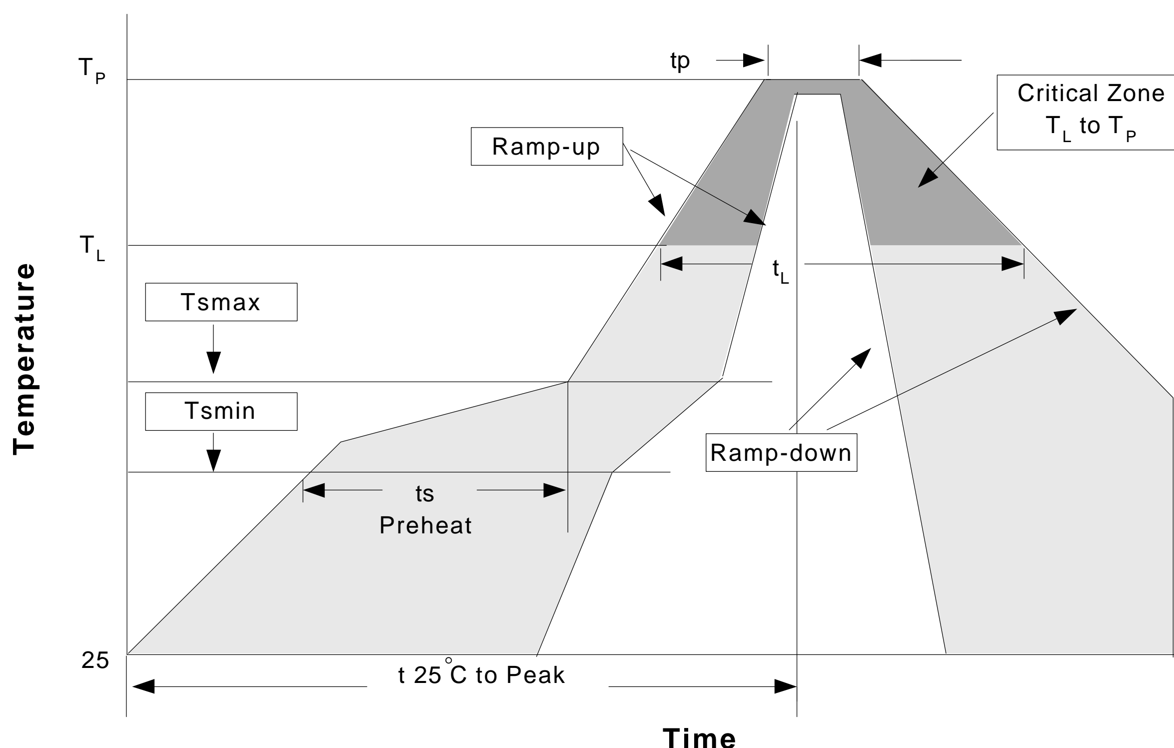
Dim	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.39	0.086	0.094
A1	0.89	1.27	0.035	0.050
b	0.508	0.89	0.020	0.035
b2	5.207	5.461	0.205	0.215
C	0.46	0.58	0.018	0.023
C1	0.46	0.58	0.018	0.023
D	5.334	6.22	0.210	0.245
D1	5.2 REF		0.205 REF	
E	6.35	6.73	0.250	0.265
E1	5.3 REF		0.209 REF	
e1	3.96	5.18	0.156	0.204
H	9.398	10.41	0.370	0.410
L	0.51		0.020	
L1	0.64	1.02	0.025	0.040
L2	0.89	2.032	0.035	0.080

Copyright © ANPEC Electronics Corp.

Physical Specifications

Terminal Material	Solder-Plated Copper (Solder Material : 90/10 or 63/37 SnPb), 100%Sn
Lead Solderability	Meets EIA Specification RSI86-91, ANSI/J-STD-002 Category 3.

Reflow Condition (IR/Convection or VPR Reflow)



Classification Reflow Profiles

Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (T_L to T_P)	3°C/second max.	3°C/second max.
Preheat - Temperature Min (Tsmin) - Temperature Max (Tsmax) - Time (min to max) (ts)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
Time maintained above: - Temperature (T_L) - Time (t_L)	183°C 60-150 seconds	217°C 60-150 seconds
Peak/Classificatioon Temperature (Tp)	See table 1	See table 2
Time within 5°C of actual Peak Temperature (tp)	10-30 seconds	20-40 seconds
Ramp-down Rate	6°C/second max.	6°C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

Notes: All temperatures refer to topside of the package .Measured on the body surface.

Copyright © ANPEC Electronics Corp.

Classification Reflow Profiles(Cont.)

Table 1. SnPb Entectic Process – Package Peak Reflow Temperatures

Package Thickness	Volume mm^3 <350	Volume mm^3 ≥350
<2.5 mm	240 +0/-5°C	225 +0/-5°C
≥2.5 mm	225 +0/-5°C	225 +0/-5°C

Table 2. Pb-free Process – Package Classification Reflow Temperatures

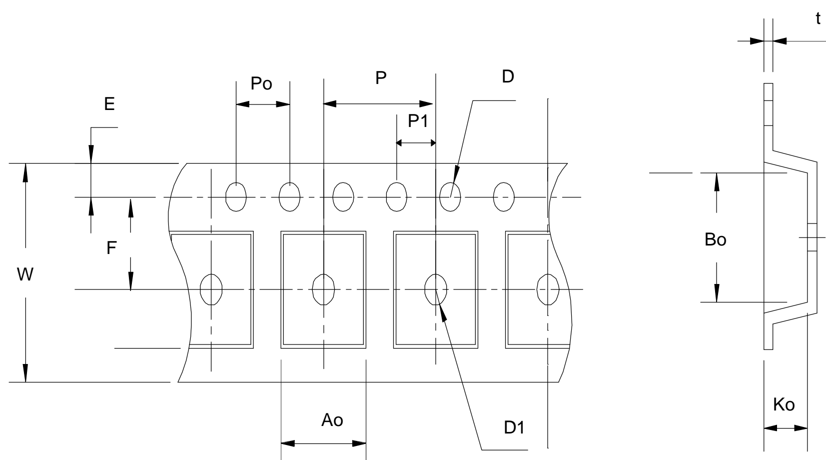
Package Thickness	Volume mm^3 <350	Volume mm^3 350-2000	Volume mm^3 >2000
<1.6 mm	260 +0°C*	260 +0°C*	260 +0°C*
1.6 mm – 2.5 mm	260 +0°C*	250 +0°C*	245 +0°C*
≥2.5 mm	250 +0°C*	245 +0°C*	245 +0°C*

*Tolerance: The device manufacturer/supplier **shall** assure process compatibility up to and including the stated classification temperature (this means Peak reflow temperature +0°C. For example 260°C+0°C) at the rated MSL level.

Reliability Test Program

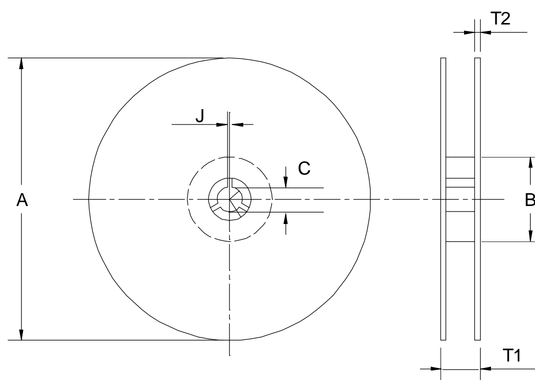
Test item	Method	Description
SOLDERABILITY	MIL-STD-883D-2003	245°C, 5 SEC
HOLT	MIL-STD-883D-1005.7	1000 Hrs Bias @125°C
PCT	JESD-22-B,A102	168 Hrs, 100%RH, 121°C
TST	MIL-STD-883D-1011.9	-65°C~150°C, 200 Cycles

Carrier Tape



Copyright © ANPEC Electronics Corp.

Carrier Tape(Cont.)



Application	A	B	C	J	T1	T2	W	P	E
TO-252	330 ±3	100 ± 2	13 ± 0. 5	2 ± 0.5	16.4 + 0.3 -0.2	2.5± 0.5	16+ 0.3 - 0.1	8 ± 0.1	1.75± 0.1
	F	**D**	**D1**	**Po**	**P1**	**Ao**	**Bo**	**Ko**	**t**
	7.5 ± 0.1	1.5 +0.1	1.5± 0.25	4.0 ± 0.1	2.0 ± 0.1	6.8 ± 0.1	10.4± 0.1	2.5± 0.1	0.3±0.05

(mm)

Cover Tape Dimensions

Application	Carrier Width	Cover Tape Width	Devices Per Reel
TO- 252	16	13.3	2500

Customer Service

Anpec Electronics Corp.

Head Office :

No.6, Dusing 1st Road, SBIP,
Hsin-Chu, Taiwan, R.O.C.
Tel : 886-3-5642000
Fax : 886-3-5642050

Taipei Branch :

7F, No. 137, Lane 235, Pac Chiao Rd.,
Hsin Tien City, Taipei Hsien, Taiwan, R. O. C.
Tel : 886-2-89191368
Fax : 886-2-89191369

Copyright © ANPEC Electronics Corp.